

Wavelength range	Type	Technology	Electrodes
Red, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

	typ. dimensions (μm)	<b>Description</b> Narrow response range (660 nm peak)  <b>Applications</b> Optical communications, safety equipment, light barriers
	typ. thickness 260 (±25) μm  anode gold alloy, 1.5 μm  cathode gold alloy, 0.5 μm	

### Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0,17	mm <sup>2</sup>
Operating temperature range		$T_{amb}$	-40 to +125	°C
Storage temperature range		$T_{stg}$	-40 to +125	°C

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Peak sensitivity wavelength	$V_R = 0\text{ V}$	$\lambda_p$		660		nm
Spectral range at 50 %	$V_R = 0\text{ V}$	$\lambda_{0.5}$	620		700	nm
Responsivity at $\lambda_p^1$	$V_R = 0\text{ V}$	$S_\lambda$		0.20		A/W
Responsivity at $\lambda_p^2$	$V_R = 0\text{ V}$	$S_\lambda$		0.42		A/W
Spectral bandwidth at 50%	$V_R = 0\text{ V}$	$\Delta\lambda_{0.5}$		80		nm
Dark current	$V_R = 1\text{ V}$	$I_D$		40	200	pA
Junction capacitance	$V_R = 0\text{ V}$	$C_J$		40		pF
Switching time	$V_R = 1\text{ V}$	$t_r, t_f$		15/30		ns

<sup>1</sup>Measured on bare chip on TO-18 header

<sup>2</sup>Measured on epoxy covered chip on TO-18 header

### Labeling

Type	Typ. $I_D$ [pA]	Typ. $S_\lambda$ [A/W]	Lot N°	Quantity
EPC-660-0.5				

**Packing:** Chips on adhesive film with wire-bond side on top

\*Note: All measurements carried out with *EPIGAP* equipment

Typical responsivity spectrum

